

Silicon NPN Power Transistors

2SC1368

DESCRIPTION

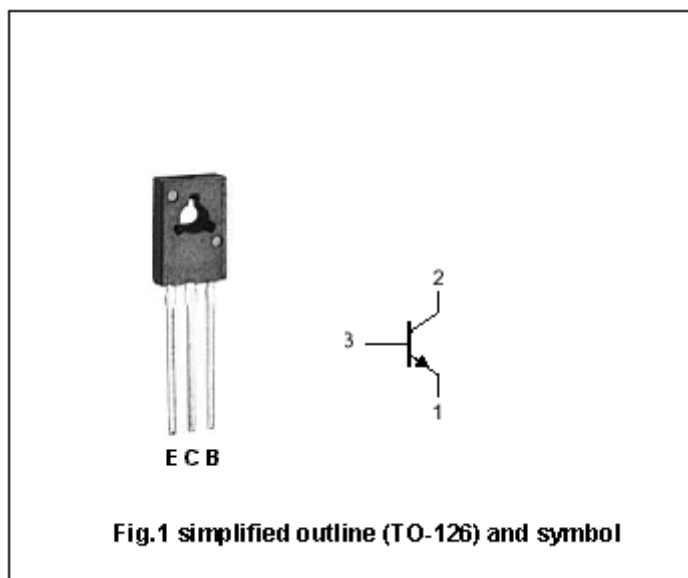
- With TO-126 package
- Low collector saturation voltage

APPLICATIONS

- For low frequency power amplifier applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	25	V
V_{CEO}	Collector-emitter voltage	Open base	25	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		1.5	A
P_C	Collector power dissipation	$T_C=25^\circ\text{C}$	8	W
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =1mA; I _B =0	25			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =50 μ A; I _E =0	25			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =50 μ A; I _B =0	5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =1.5A; I _B =0.15A			0.8	V
I _{CBO}	Collector cut-off current	V _{CB} =25V; I _E =0			1.0	μ A
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			1.0	μ A
h _{FE}	DC current gain	I _C =0.5A ; V _{CE} =2V	60		320	
f _T	Transition frequency	I _C =0.5A ; V _{CE} =5V		180		MHz

PACKAGE OUTLINE

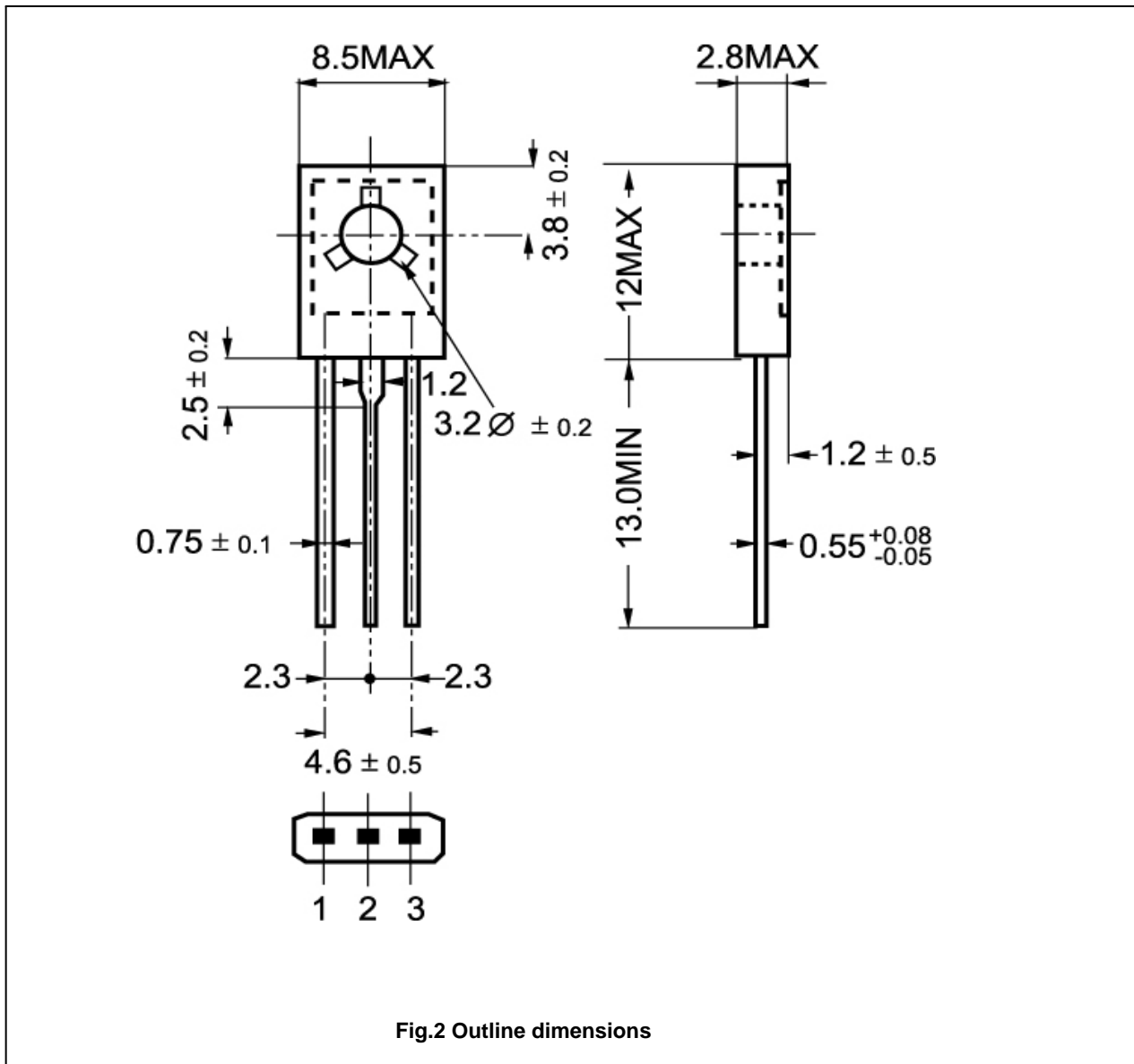


Fig.2 Outline dimensions